



2N7002W

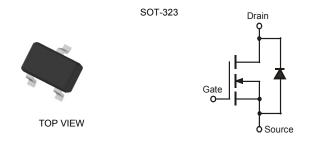
N-CHANNEL ENHANCEMENT MODE FIELD EFFECT TRANSISTOR

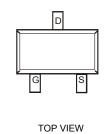
Features

- Low-On Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Ultra-Small Surface Mount Package
- Totally Lead-Free & Fully RoHS compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: SOT-323
- Case Material: Molded Plastic, "Green" Molding Compound, Note 4. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminals: Finish Matte Tin annealed over Alloy 42 leadframe. Solderable per MIL-STD-202, Method 208
- Terminal Connections: See Diagram
- Weight: 0.006 grams (approximate)





Equivalent Circuit

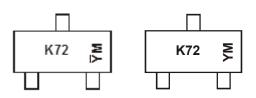
Ordering Information (Notes 4)

Part Number	Case	Packaging
2N7002W-7-F	SOT-323	3000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html

Marking Information



Chengdu A/T Site Shanghai A/T Site

K72 = Product Type Marking Code

YM = Date Code Marking for SAT (Shanghai Assembly/ Test site) YM = Date Code Marking for CAT (Chengdu Assembly/ Test site) Y or \overline{Y} = Year (ex: A = 2013)

M = Month (ex: 9 = September)

Date Code Key

Year	2012	2	2013		2014	20	15	2016		2017	2	2018
Code	Z		Α		В	(2	D		Е		F
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteris	Symbol	Value	Unit	
Drain-Source Voltage		V_{DSS}	60	V
Drain-Gate Voltage $R_{GS} \le 1.0 M\Omega$		V_{DGR}	60	V
Gain-Source Voltage	Continuous Pulsed	V_{GSS}	±20 ±40	V
Drain Current (Note 5)	Continuous Continuous @ +100°C Pulsed	I _D	115 73 800	mA

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	D	200	mW
Derating above T _A = +25°C	P_{D}	1.60	mW
Thermal Resistance, Junction to Ambient	$R_{ hetaJA}$	625	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

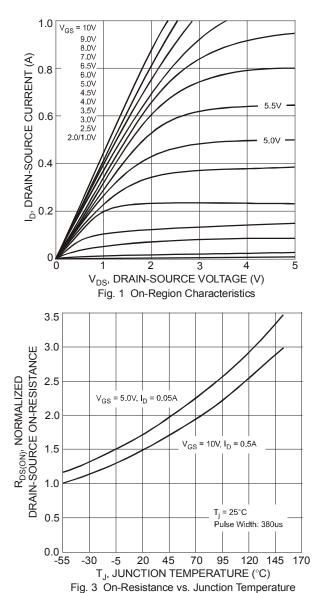
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

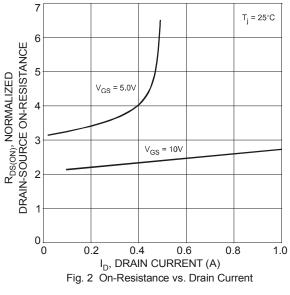
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 6)						
Drain-Source Breakdown Voltage	BV _{DSS}	60	70	_	V	$V_{GS} = 0V, I_D = 10\mu A$
Zero Gate Voltage Drain Current @ T _C = +25°0	C I _{DSS}			1.0	μА	V _{DS} = 60V, V _{GS} = 0V
@ T _C = +125°C	1500			500	P** :	100 111, 100 11
Gate-Body Leakage	I _{GSS}		_	±10	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 6)	•		•	•	-	
Gate Threshold Voltage	V _{GS(th)}	1.0	_	2.0	V	$V_{DS} = V_{GS}$, $I_D = 250\mu A$
Static Drain-Source On-Resistance @ T _J = +25°0	C B		1.8	7.5	Ω	$V_{GS} = 5.0V, I_D = 0.05A$
@ T _j = +125°C	R _{DS(ON)}		2.6	13.5	12	$V_{GS} = 10V, I_D = 0.5A$
On-State Drain Current	I _{D(ON)}	0.5	1.0	_	Α	V _{GS} = 10V, V _{DS} = 7.5V
Forward Transconductance	9 FS	80			mS	$V_{DS} = 10V, I_D = 0.2A$
DYNAMIC CHARACTERISTICS (Note 7)	_					
Input Capacitance	C _{iss}	_	22	50	pF	V 05V V 0V
Output Capacitance Reverse Transfer Capacitance		_	11	25	pF	V _{DS} = 25V, V _{GS} = 0V f = 1.0MHz
			2.0	5.0	pF	1 = 1.0WH12
SWITCHING CHARACTERISTICS (Note 7)						
Turn-On Delay Time	t _{D(ON)}	_	7.0	20	ns	$V_{DD} = 30V, I_D = 0.2A,$
Turn-Off Delay Time	t _{D(OFF)}		11	20	ns	R_L = 150 Ω , V_{GEN} = 10 V , R_{GEN} = 25 Ω

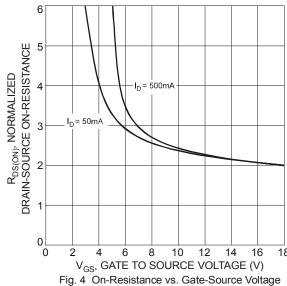
Notes:

- 5. Device mounted on FR-4 PCB 1.0 x 0.75 x 0.062 inch pad layout as shown on Diodes, Inc. suggested pad layout AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.
- 6. Short duration pulse test used to minimize self-heating effect.
- 7. Guaranteed by design. Not subject to production testing.

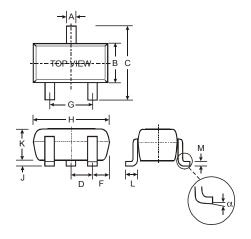








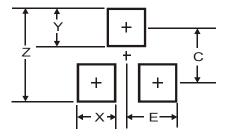
Package Outline Dimensions



SOT-323					
Dim	Min	Max			
Α	0.25	0.40			
В	1.15	1.35			
С	2.00	2.20			
D	0.65 N	ominal			
F	0.30	0.40			
G	1.20	1.40			
Н	1.80	2.20			
J	0.0	0.10			
K	0.90	1.00			
L	0.25	0.40			
М	0.10	0.18			
α	0°	8°			
All Dimensions in mm					



Suggested Pad Layout



Dimensions	Value (in mm)
Z	2.8
Х	0.7
Υ	0.9
С	1.9
E	1.0

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